

REMARKS/ARGUMENTS

Reconsideration of this application and favorable action are solicited. Claims 1-7 remain active in the case.

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1. 112 rejections over claims 1 and 5-7:

Claims 1 and 5-7 have been amended to overcome 112 rejections. The clerical errors in claims 5-7 have been corrected. The amendments to the claims are fully supported by the detailed description and the figures thereof. No new matter is introduced. Reconsideration of claims 1 and 5-7 is politely requested.

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2. 103(a) rejections over claims 1-4:

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Claim 1 was rejected under 35 USC 103 (a), for reason of record that can be found on pages 3-5 in the Office action identified above, which is Part of Paper No./Mail Date 20060915.

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Claim 1 was rejected because of Chu (U.S. 6,346,366) in view of Koenig (U.S. 2004/0224524) and Demaray (U.S. 6,533,907). Chu teaches a method for making a guard ring on a merged DRAM integrated circuit. Chu teaches using the photoresist mask and anisotropic etching to pattern the stacked film (16, 18, 20) for the FET gate electrodes in the memory region and to concurrently form the wider guard rings in the stacked film over the edge of the amorphous silicon layer. Koenig teaches a lithographic mask fabrication method comprising non-selectively blanket depositing a conformal sacrificial coating 40 both on the metal-containing layer 15 and on the sidewalls and top surface of the resist pattern 32 (Fig. 3). Demaray teaches a method of making amorphous silicon material.

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The applicants submit that the cited prior art references fail to anticipate or render

obvious, the limitations "selectively sputtering a silicon thin film *merely on said top surface and said vertical sidewalls of said photoresist pattern, but substantially not on said cap layer*; wherein thickness of said silicon thin film on said vertical sidewalls is "x", while thickness of said silicon thin film on said top surface is "y", and $x \neq y$ ", as

5 required in the amended claim 1. It is respectfully noted that the silicon thin film is not conformal coating and is merely coated on the sidewalls and top surface of the photoresist pattern, as specifically indicated in Fig. 4 of this application. Reconsideration of the amended claim 1 is requested.

10 As Claims 2-7 are dependent upon claim 1, they should be allowable if claim 1 is allowed. Reconsideration of claims 2-7 is therefore politely requested. Applicant respectfully requests that a timely Notice of Allowance be issued in this case.

Sincerely yours,

15 Winston Hsu

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